

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	19mΩ @ V _{GS} = 4.5V	15A
	25mΩ @ V _{GS} = 2.5V	14A
	40mΩ @ V _{GS} = 1.8V	10A
	120mΩ @ V _{GS} = 1.5V	6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

Features

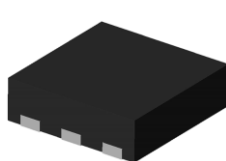
- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- The DMN3020UFDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

<https://www.diodes.com/quality/product-definitions/>

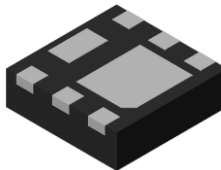
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ4
- Weight: 0.007 Grams (Approximate)

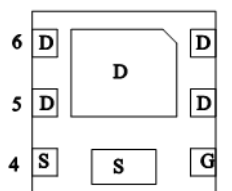
U-DFN2020-6 (Type F)



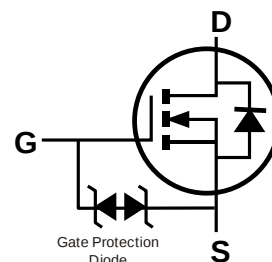
Top View



Bottom View



Pin Out
Bottom View



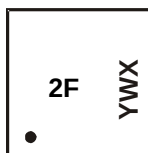
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3020UFDQ-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN3020UFDQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



2F = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 1 = 2021)
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	1	2	3	4	5	6	7	8	9	0	1	2

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _C = +25°C T _C = +70°C	I _D	15 13	A
	t < 5s	T _A = +25°C T _A = +70°C	I _D	10.4 8.3	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	40	A
Continuous Source-Drain Diode Current (Note 6)			I _S	2.2	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	17	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	15	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.73	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	171	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.03	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	63	°C/W
Thermal Resistance, Junction to Case	Steady State	R _{θJC}	18	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.4	0.6	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	16	19	mΩ	V _{GS} = 4.5V, I _D = 4.5A
			19	25		V _{GS} = 2.5V, I _D = 3.5A
			26	40		V _{GS} = 1.8V, I _D = 2.0A
			32	120		V _{GS} = 1.5V, I _D = 1.0A
			—	—		V _{GS} = 1.5V, I _D = 1.0A
Diode Forward Voltage	V _{SD}	—	0.6	1.2	V	V _{GS} = 0V, I _S = 1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1304	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	87	—		
Reverse Transfer Capacitance	C _{rss}	—	80	—		
Gate Resistance	R _g	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	15	—	nC	V _{DS} = 15V, I _D = 4.5A
Total Gate Charge (V _{GS} = 8V)	Q _g	—	27	—		
Gate-Source Charge	Q _{gs}	—	2.0	—		
Gate-Drain Charge	Q _{gd}	—	2.1	—		
Turn-On Delay Time	t _{D(ON)}	—	4.1	—	ns	V _{DS} = 15V, V _{GS} = 4.5V, R _G = 1Ω, I _D = 4.5A
Turn-On Rise Time	t _r	—	4.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	20.5	—		
Turn-Off Fall Time	t _f	—	3.2	—		
Reverse Recovery Time	t _{RR}	—	7.1	—	ns	I _F = 1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	1.7	—	nC	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

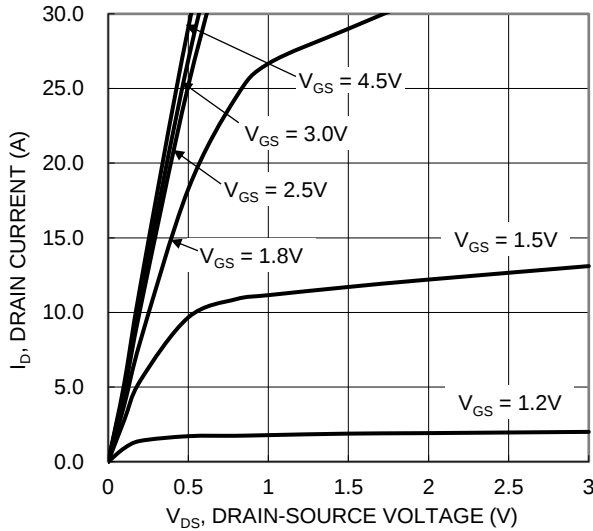


Figure 1. Typical Output Characteristic

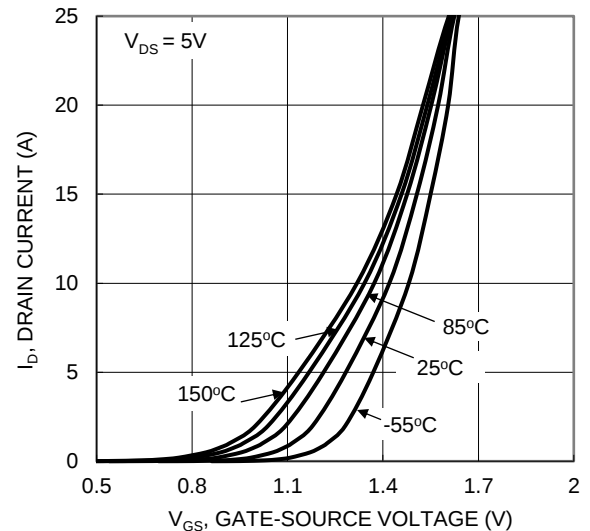


Figure 2. Typical Transfer Characteristic

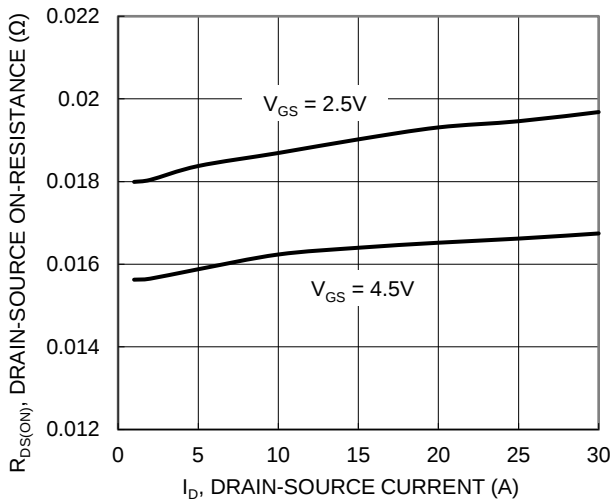


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

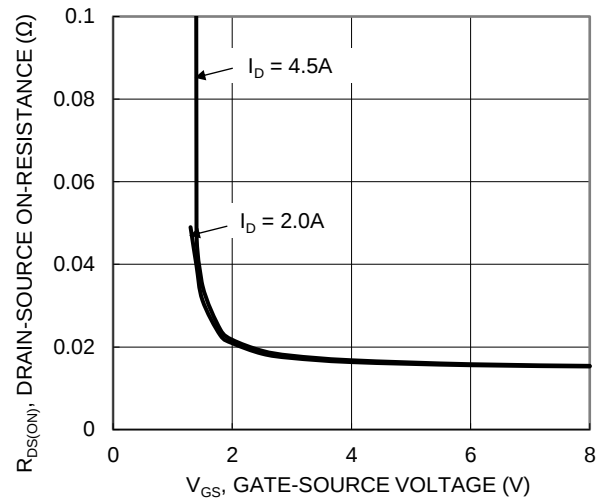


Figure 4. Typical Transfer Characteristic

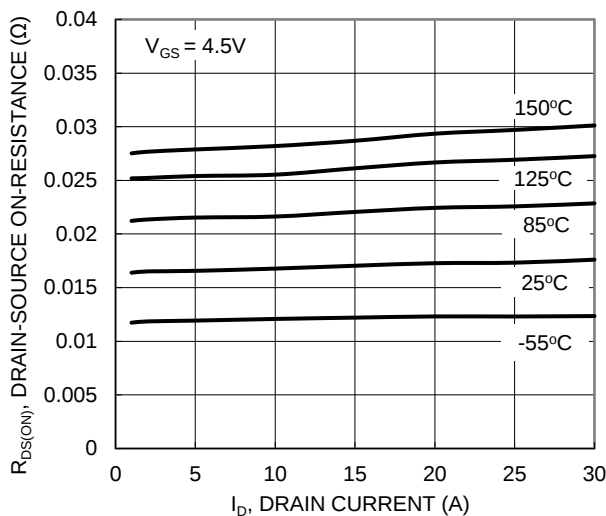


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

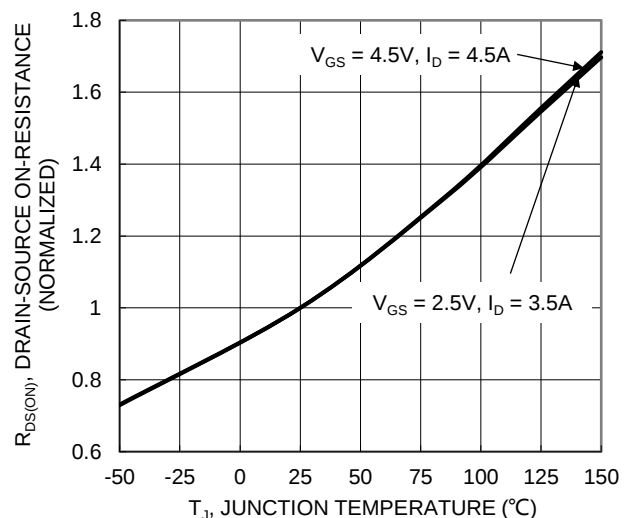


Figure 6. On-Resistance Variation with Temperature

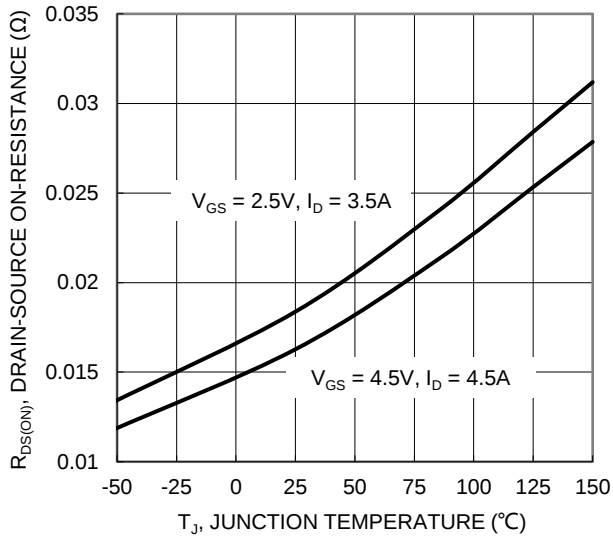


Figure 7. On-Resistance Variation with Temperature

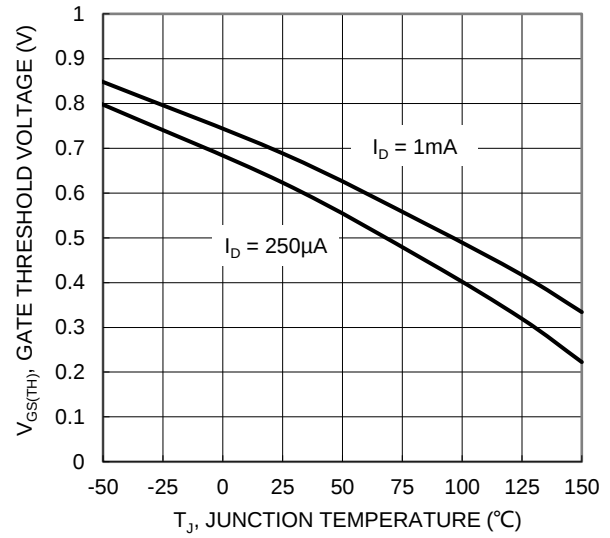


Figure 8. Gate Threshold Variation vs. Temperature

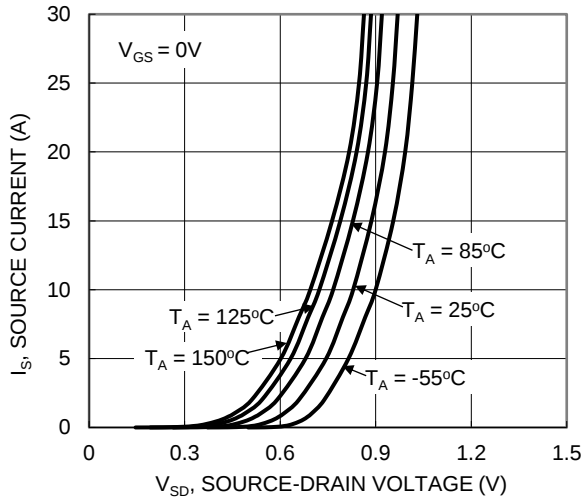


Figure 9. Diode Forward Voltage vs. Current

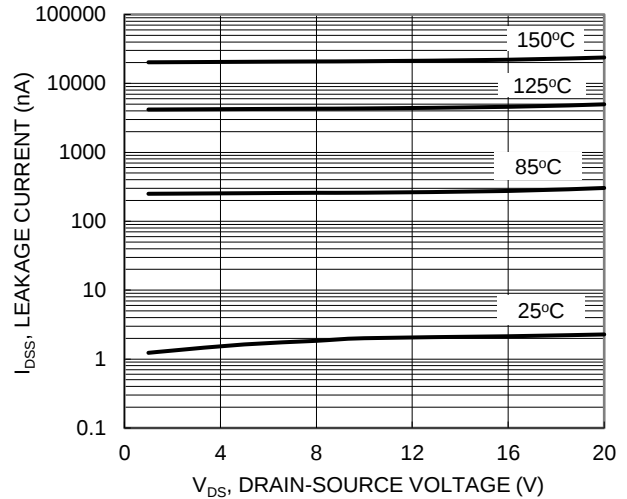


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

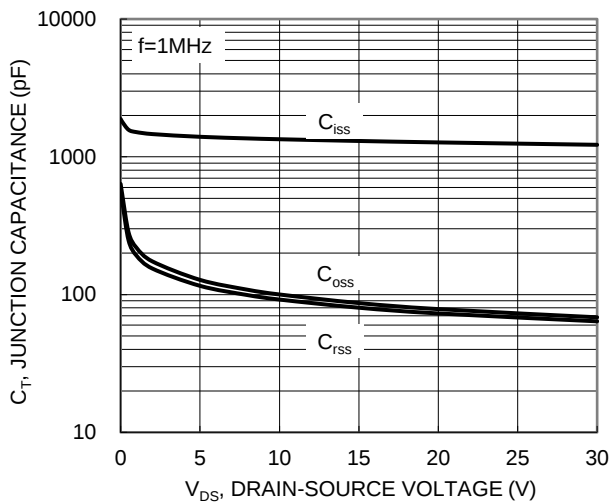


Figure 11. Typical Junction Capacitance

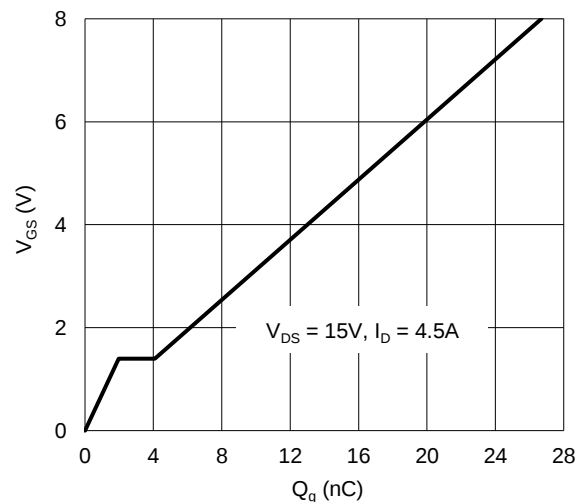
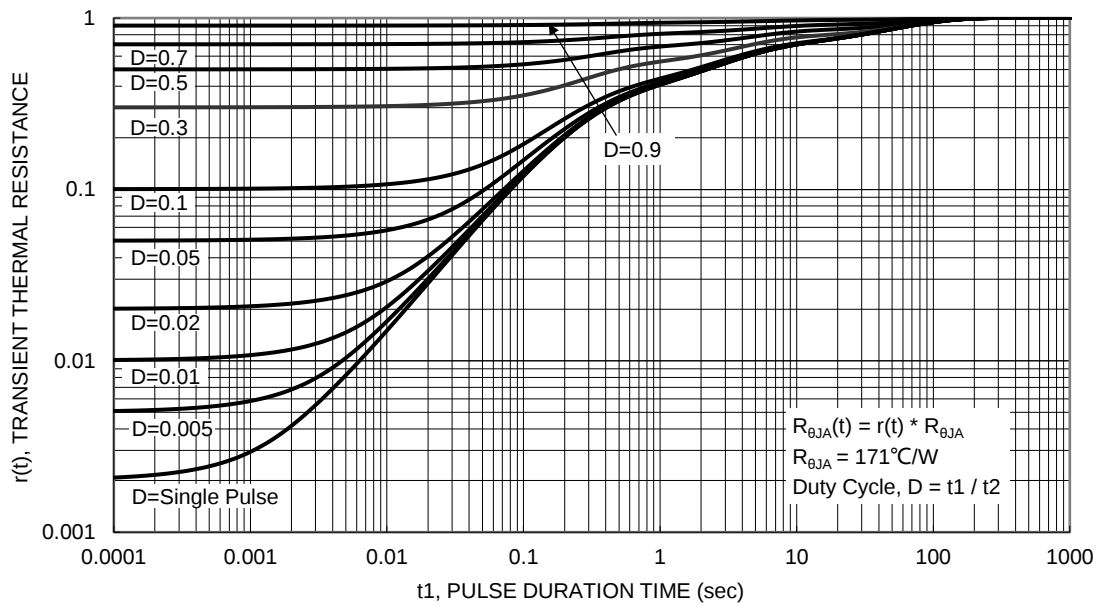
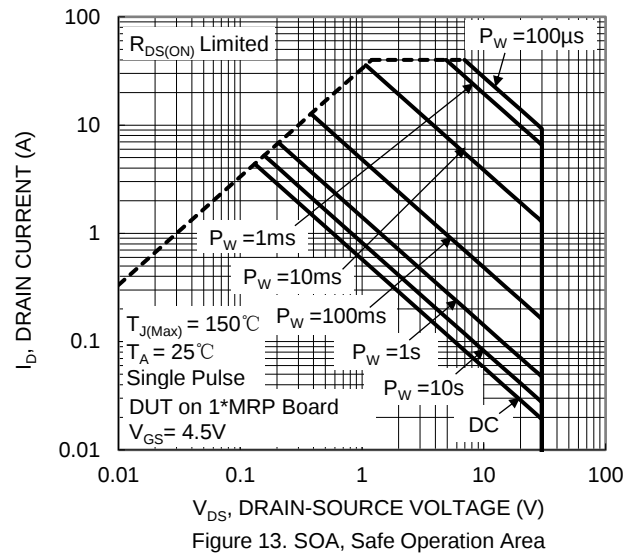


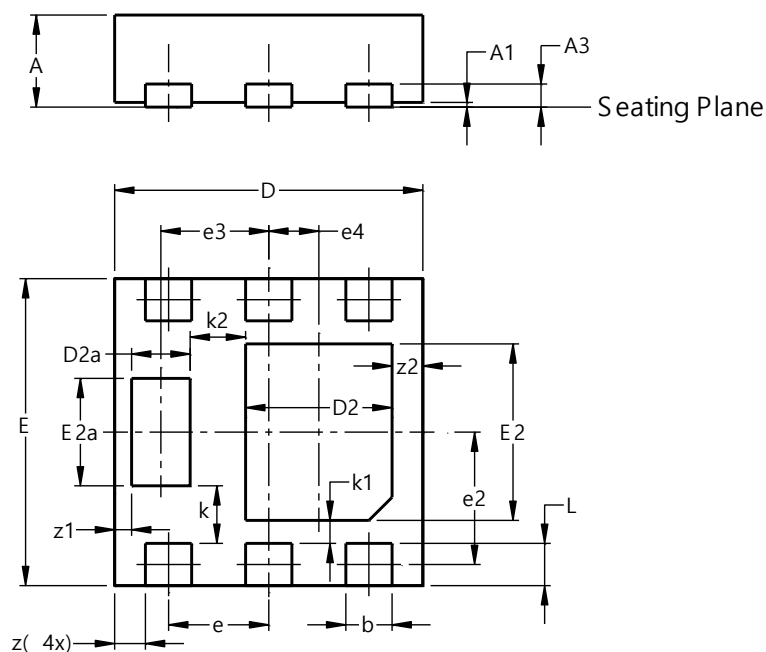
Figure 12. Gate Charge



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

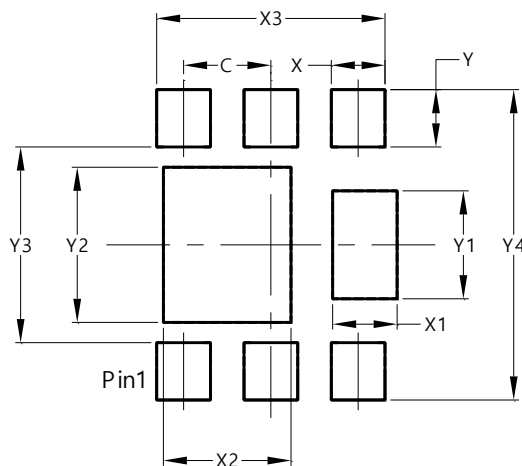


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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